EL2252D Die

Dual 50 MHz Comparator/Pin Receiver

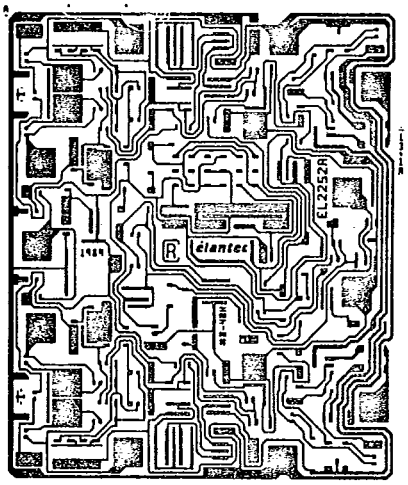
T-45-17

Absolute Maximum Ratings (T_A = 25°C)

	Voltage between V+ and V−	36V
	Voltage at V+	18V
	Voltage between −IN and +IN Pins	36V
	Output Current	12 mA
	Current into +IN, −IN, HYS, or /TTL	5 mA
T_J	Maximum Junction Temperature	175°C

Important Note:
For AC electrical characteristics, refer to the typical electrical table and performance curves in the package data sheet. These characteristics are guaranteed but not tested in die form. Unless otherwise noted, all tests are pulsed tests, therefore $T_J = T_C = T_A$.

Test Level	Test Procedure
I	100% production tested in wafer form. See remarks under Electrical Testing in the General Die section.



DIE SIZE: 65 x 77 MILS

DC Electrical Characteristics V_S = ±15V; HYS and i/m TTL grounded; T_A = 25°C

Parameter	Description	Min	Typ	Max	Test Level	Units
V_{OS}	Input Offset Voltage		1	6	I	mV
I_B	Input Bias Current V_{CM} = 0V, pin 2 or 3		6	12	I	µA
I_{OS}	Input Offset Current V_{CM} = 0V		0.2	1	I	µA
CMRR	Common-Mode Rejection Ratio (Note 1)	70	95		I	dB
PSRR	Power Supply Rejection Ratio (Note 2)	70	90		I	dB
V_{CM}+ V_{CM}−	Common Mode Input Range	10	13		I	V
		−9	−12		I	V
A_{VOL}	Large Signal Voltage Gain (V_{OUT} = 0.8V +0.20V)	4,000	8,000		I	V/V
V_{OL}	Output Voltage Logic Low I_{OL} = 0 MA	−0.2	0.2	0.4	I	V
	I_{OL} = 5 MA	−0.2	0.4	0.8	I	V
V_{OH}	Output Voltage Logic High CMOS Mode	4	4.6	5.1	I	V
	TTL Mode	2.4	2.7	3.2	I	V
I_S+	Positive Supply Current		16	19	I	mA
I_S−	Negative Supply Current		17	20	I	mA

Note 1: Two tests are performed with V_{CM} = 0V to −9V and V_{CM} = 0V to 10V.
Note 2: Two tests are performed with V+ = +15V, V− changed from −10V to −15V; V− = −15V, V+ changed from 10V to 15V.